

## IN THE SPECIFICATION

At page 7, line 5, please insert the following sentence:

Figs. 18a and 18b are cross-sectional views of one embodiment of a trench-gated and surface-gated IGBTs of the present invention.

At page 10 of the specification, following the last paragraph, please insert the following two paragraphs:

Referring now to Fig. 18a, one embodiment of a trench-gated IGBT of the present invention is shown. IGBT 100 includes a plurality of N<sup>+</sup> source contact regions 20 (only two of which are shown) that extend between the base regions 3 and source stripes 2a, 2b, and which are spaced apart along the length of the base stripes 3 and source stripes 2a and 2b. Insulating layer 21, in this embodiment, entirely covers the trench gate 19 and source stripes 2a and 2b. A plurality of vias 102 (only two shown) are formed in known manner through insulating layer 21 over source contact regions 20. Source contact layer 23 is disposed over the insulating later 21, and extends through vias 102 to thereby contact the source contact regions 20.

Referring now to Fig. 18b, one embodiment of a surface-gated IGBT of the present invention is shown. IGBT 200 includes a plurality of N<sup>+</sup> source contact regions 20 (only one shown) that extend between the body stripe and the source stripes 2a, 2b, and which are spaced apart along the length of the base stripes 3 and source stripes 2a and 2b. Insulating layer 17, in this embodiment, entirely covers source stripes 2a and 2b. A plurality of vias 102 (only one shown) are formed in known manner through insulating layer 17 over source contact regions 20. Source contact layer 23 is disposed over the insulating layers 21 and 17, and extends through vias 102 to thereby contact source contact regions 20.